



BD439 BD440
BD441 BD442

EPIAXIAL-BASE NPN/PNP

MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS

The BD 439 and BD 441 are silicon epitaxial-base NPN power transistors in Jedec TO-126 plastic package, intended for use in power linear and switching applications. The complementary PNP types are the BD 440 and BD 442 respectively.

ABSOLUTE MAXIMUM RATINGS

	NPN PNP*	BD439 BD440	BD441 BD442
V_{CBO}	Collector-base voltage ($I_E = 0$)	60V	80V
V_{CES}	Collector-emitter voltage ($V_{BE} = 0$)	60V	80V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	60V	80V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5V	
I_C	Collector current	4A	
I_{CM}	Collector peak current ($t \leq 10ms$)	7A	
I_B	Base current	1A	
P_{tot}	Total power dissipation at $T_{case} \leq 25^\circ C$	36W	
T_{stg}	Storage temperature	-65 to $150^\circ C$	
T_j	Junction temperature		$150^\circ C$

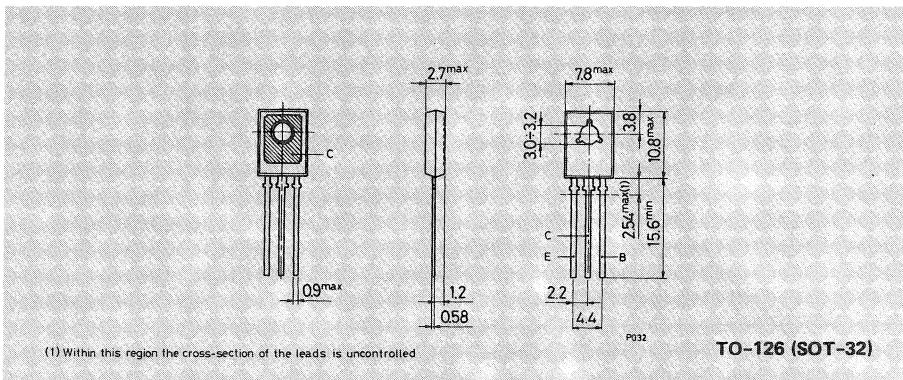
* For PNP types voltage and current values are negative

INTERNAL SCHEMATIC DIAGRAMS



MECHANICAL DATA

Dimensions in mm



(1) Within this region the cross-section of the leads is uncontrolled

TO-126 (SOT-32)



BD439 BD440
BD441 BD442

THERMAL DATA

$R_{th\ j\text{-}case}$	Thermal resistance junction-case	max	3.5	$^{\circ}\text{C}/\text{W}$
$R_{th\ j\text{-}amb}$	Thermal resistance junction-ambient	max	100	$^{\circ}\text{C}/\text{W}$

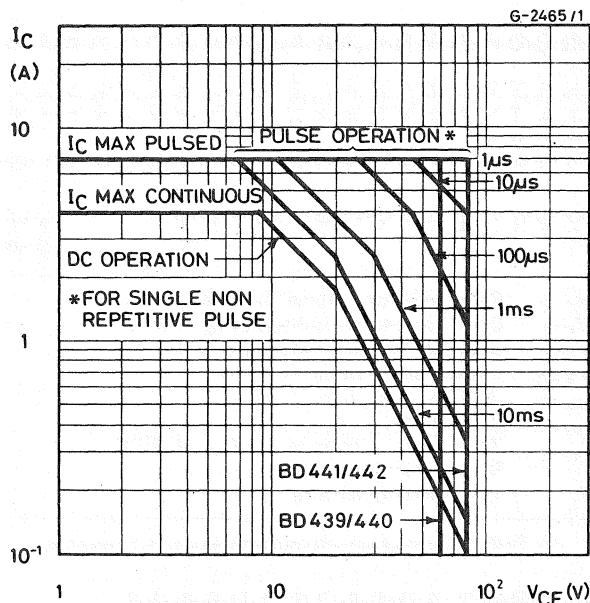
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector cutoff current ($I_E = 0$)	for BD439/40 for BD441/42	$V_{CB} = 60\text{V}$ $V_{CB} = 80\text{V}$	100 100	100 100	μA μA
I_{CES}	Collector cutoff current ($V_{BE} = 0$)	for BD439/40 for BD441/42	$V_{CE} = 60\text{V}$ $V_{CE} = 80\text{V}$	100 100	100 100	μA μA
I_{EBO}	Emitter cutoff current ($I_C = 0$)	$V_{EB} = 5\text{V}$		1	1	mA
$V_{CEO\ (sus)}$ *	Collector-emitter sustaining voltage ($I_B = 0$)	$I_C = 100\text{mA}$	for BD439/40 for BD441/42	60 80	60 80	V V
$V_{CE\ (sat)}$ *	Collector-emitter saturation voltage	$I_C = 2\text{A}$	$I_B = 0.2\text{A}$	0.8	0.8	V
V_{BE} *	Base-emitter voltage	$I_C = 10\text{ mA}$ $I_C = 2\text{ A}$	$V_{CE} = 5\text{V}$ $V_{CE} = 1\text{V}$	0.58 1.5	0.58 1.5	V V
h_{FE} *	DC current gain	$I_C = 10\text{ mA}$ $I_C = 500\text{mA}$ $I_C = 2\text{ A}$	$V_{CE} = 5\text{V}$ for BD439/40 for BD441/42 $V_{CE} = 1\text{V}$ for BD439/40 for BD441/42 $V_{CE} = 1\text{V}$ for BD439/40 for BD441/42	20 15 40 40 25 15	130 130 140 140 — —	— — — — — —
h_{FE_1}/h_{FE_2} *Matched pair		$I_C = 500\text{mA}$	$V_{CE} = 1\text{V}$	1.4	1.4	—
f_T	Transition frequency	$I_C = 250\text{mA}$	$V_{CE} = 1\text{V}$	3	3	MHz

* Pulsed: pulse duration = 300 μs , duty cycle = 1.5%

For PNP types voltage and current values are negative

Safe operating areas



For the others characteristic curve see the BD433/BD434 series